

Title (en)

METHOD FOR PRODUCING HIGH PURITY SILICON

Title (de)

VERFAHREN ZUR HERSTELLUNG VON HOCHREINEM SILICIUM

Title (fr)

METHODE DE FABRICATION DE SILICIUM DE HAUTE PURETE

Publication

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Application

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Abstract (en)

[origin: WO2006095662A1] An object of the invention is to provide a method for producing a large amount of inexpensive high purity silicon useful for a solar battery. Disclosed is a method for producing high purity silicon by migrating impurities in silicon to slag including performing a first slag purification of a first silicon, separating the slag from the first silicon after finishing the first slag purification, and feeding the separated slag to a second molten silicon in a second purification of the second silicon, wherein purity of said second silicon prior to purification is lower than purity of the first silicon after purification.

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